

ON THE MODEL OF RADIATION-INDUCED  
ORDERING OF THE DEFECT STRUCTURE  
IN CdS CRYSTALS

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S u m m a r y

A physical and mathematical model of the radiation-induced ordering of the defect structure in CdS crystals is proposed. The key points of the model are the gettering of defects ( $Cd_i$ ) at sinks with regard for a substantial (by about 2 orders of magnitude) increase of the diffusion coefficient of defects under irradiation and the increase of the defect lifetime at irradiation doses below 750 R.